TECHNICAL DATA
DATA SHEET 642, REV. A
Formerly part number SHD1162/A/B

SILICON SCHOTTKY RECTIFIER Very Low Forward Voltage Drop

Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	45	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form	15	Α
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave	280	Α
Non-Repetitive Avalanche Energy	E _{AS}	$T_J = 25 ^{\circ}\text{C}, I_{AS} = 3.0 \text{A}, \\ L = 4.4 \text{mH}$	20	mJ
Repetitive Avalanche Current	I _{AR}	I_{AS} decay linearly to 0 in 1 μ s f limited by T_J max V_A =1.5 V_R	3.0	А
Maximum Thermal Resistance	$R_{ ext{ hetaJC}}$	(Junction to Mounting Surface, Cathode)	.85	°C/W
Max. Junction Temperature	T_J	-	-65 to +175	°C
Max. Storage Temperature	T_{stg}	-	-65 to +175	°C

Electrical Characteristics

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 15A, Pulse, T _J = 25 °C	0.64	V
	V _{F2}	@ 15A, Pulse, T _J = 125 °C	0.57	V
Max. Reverse Current	I _{R1}	@V _R = 45V, Pulse,	400	μΑ
		T _J = 25 °C		
	I_{R2}	@V _R = 45V, Pulse,	15	mA
		T _J = 125 °C		
Max. Junction Capacitance	C _T	$@V_R = 5V, T_C = 25 ^{\circ}C$	800	pF
		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV} \text{ (p-p)}$		

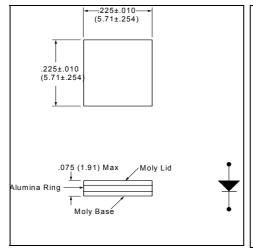
SHD-1E

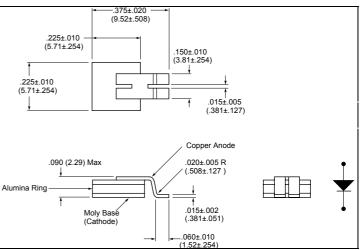
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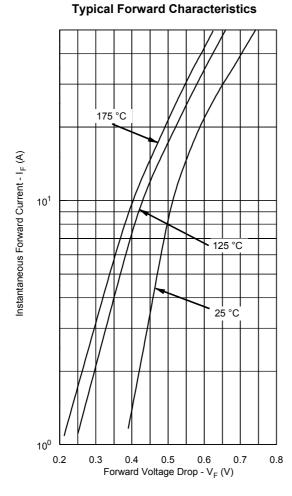
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DATA SHEET 642, REV. A Formerly part number SHD1162/A/B

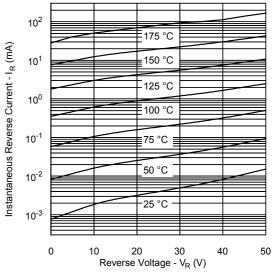
MECHANICAL DIMENSIONS: In Inches / mm



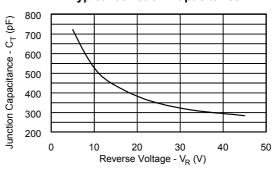




Typical Reverse Characteristics



Typical Junction Capacitance



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